

TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL TYPE

# 2SC4707

LOW FREQUENCY AMPLIFIER APPLICATIONS.

DRIVER STAGE AMPLIFIER APPLICATIONS.

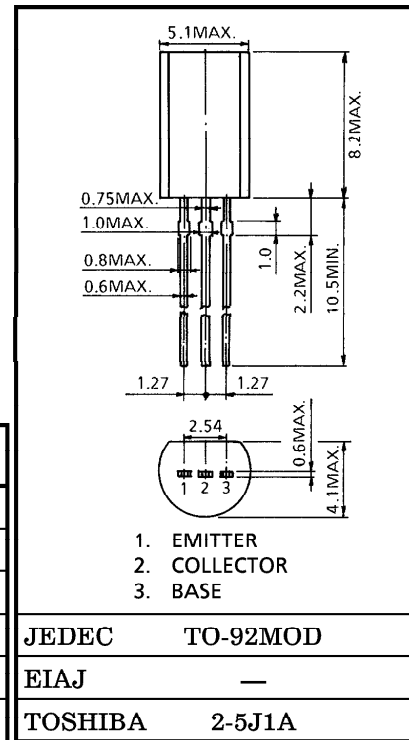
SWITCHING APPLICATIONS.

- Excellent  $h_{FE}$  Linearity  
:  $h_{FE(2)} = 35$  (Min.), ( $V_{CE} = 2V, I_C = 300mA$ )
- Complementary to 2SA1811

MAXIMUM RATINGS ( $T_a = 25^\circ C$ )

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	$V_{CBO}$	35	V
Collector-Emitter Voltage	$V_{CEO}$	30	V
Emitter-Base Voltage	$V_{EBO}$	5	V
Collector Current	$I_C$	500	mA
Base Current	$I_B$	100	mA
Collector Power Dissipation	$P_C$	800	mW
Junction Temperature	$T_j$	150	$^\circ C$
Storage Temperature Range	$T_{stg}$	-55~150	$^\circ C$

Unit in mm



JEDEC TO-92MOD

EIAJ —

TOSHIBA 2-5J1A

Weight : 0.36g

ELECTRICAL CHARACTERISTICS ( $T_a = 25^\circ C$ )

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	$I_{CBO}$	$V_{CB} = 35V, I_E = 0$	—	—	0.1	$\mu A$
Emitter Cut-off Current	$I_{EBO}$	$V_{EB} = 5V, I_C = 0$	—	—	0.1	$\mu A$
DC Current Gain	$h_{FE(1)}$	$V_{CE} = 2V, I_C = 100mA$	100	—	300	
	$h_{FE(2)}$	$V_{CE} = 2V, I_C = 300mA$	35	—	—	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 300mA, I_B = 30mA$	—	0.2	0.5	V
Base-Emitter Voltage	$V_{BE}$	$V_{CE} = 2V, I_C = 100mA$	—	0.8	1.0	V
Transition Frequency	$f_T$	$V_{CE} = 6V, I_C = 20mA$	—	300	—	MHz
Collector Output Capacitance	$C_{ob}$	$V_{CB} = 6V, I_E = 0, f = 1MHz$	—	7	—	pF

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